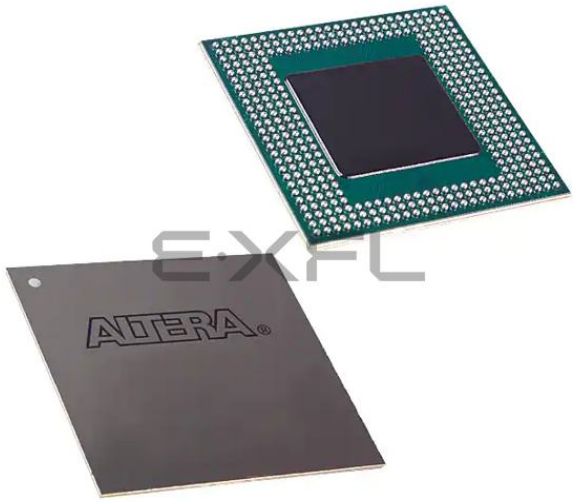

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	246
Number of Gates	263000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	356-LBGA
Supplier Device Package	356-BGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k100ebc356-3n

Table 2. Additional APEX 20K Device Features *Note (1)*

Feature	EP20K300E	EP20K400	EP20K400E	EP20K600E	EP20K1000E	EP20K1500E
Maximum system gates	728,000	1,052,000	1,052,000	1,537,000	1,772,000	2,392,000
Typical gates	300,000	400,000	400,000	600,000	1,000,000	1,500,000
LEs	11,520	16,640	16,640	24,320	38,400	51,840
ESBs	72	104	104	152	160	216
Maximum RAM bits	147,456	212,992	212,992	311,296	327,680	442,368
Maximum macrocells	1,152	1,664	1,664	2,432	2,560	3,456
Maximum user I/O pins	408	502	488	588	708	808

Note to Tables 1 and 2:
(1) The embedded IEEE Std. 1149.1 Joint Test Action Group (JTAG) boundary-scan circuitry contributes up to 57,000 additional gates.

Additional Features

- Designed for low-power operation
  - 1.8-V and 2.5-V supply voltage (see Table 3)
  - MultiVolt™ I/O interface support to interface with 1.8-V, 2.5-V, 3.3-V, and 5.0-V devices (see Table 3)
  - ESB offering programmable power-saving mode

Table 3. APEX 20K Supply Voltages

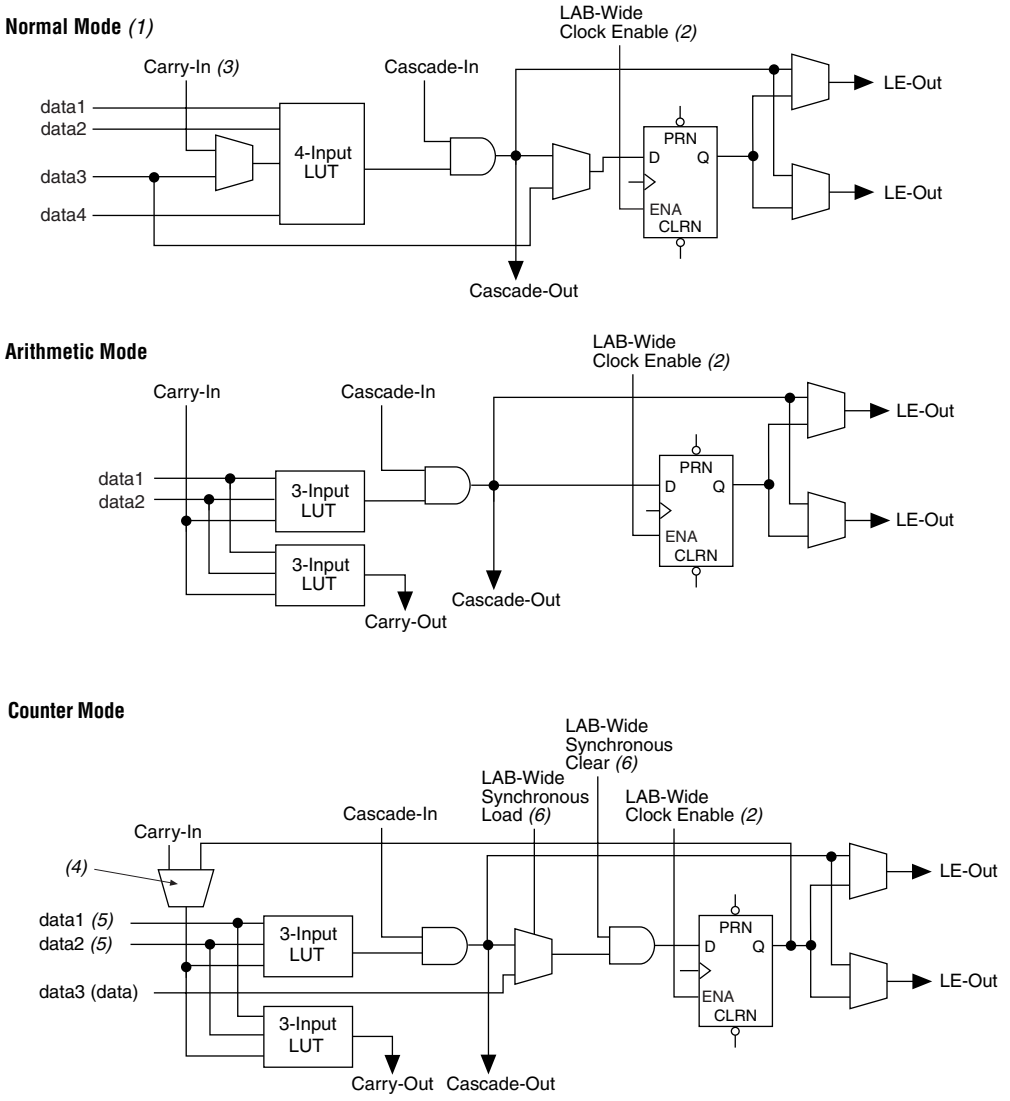
Feature	Device	
	EP20K100 EP20K200 EP20K400	EP20K30E EP20K60E EP20K100E EP20K160E EP20K200E EP20K300E EP20K400E EP20K600E EP20K1000E EP20K1500E
Internal supply voltage (V_{CCINT})	2.5 V	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	2.5 V, 3.3 V, 5.0 V	1.8 V, 2.5 V, 3.3 V, 5.0 V *(1)*

Note to Table 3:
(1) APEX 20KE devices can be 5.0-V tolerant by using an external resistor.

Table 8. Comparison of APEX 20K & APEX 20KE Features

Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V_{CCIO} V_{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

Figure 8. APEX 20K LE Operating Modes



Notes to Figure 8:

(1) LEs in normal mode support register packing.
(2) There are two LAB-wide clock enables per LAB.
(3) When using the carry-in in normal mode, the packed register feature is unavailable.
(4) A register feedback multiplexer is available on LE1 of each LAB.
(5) The DATA1 and DATA2 input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in an LAB.
(6) The LAB-wide synchronous clear and LAB wide synchronous load affect all registers in an LAB.

Figure 12. APEX 20KE FastRow Interconnect

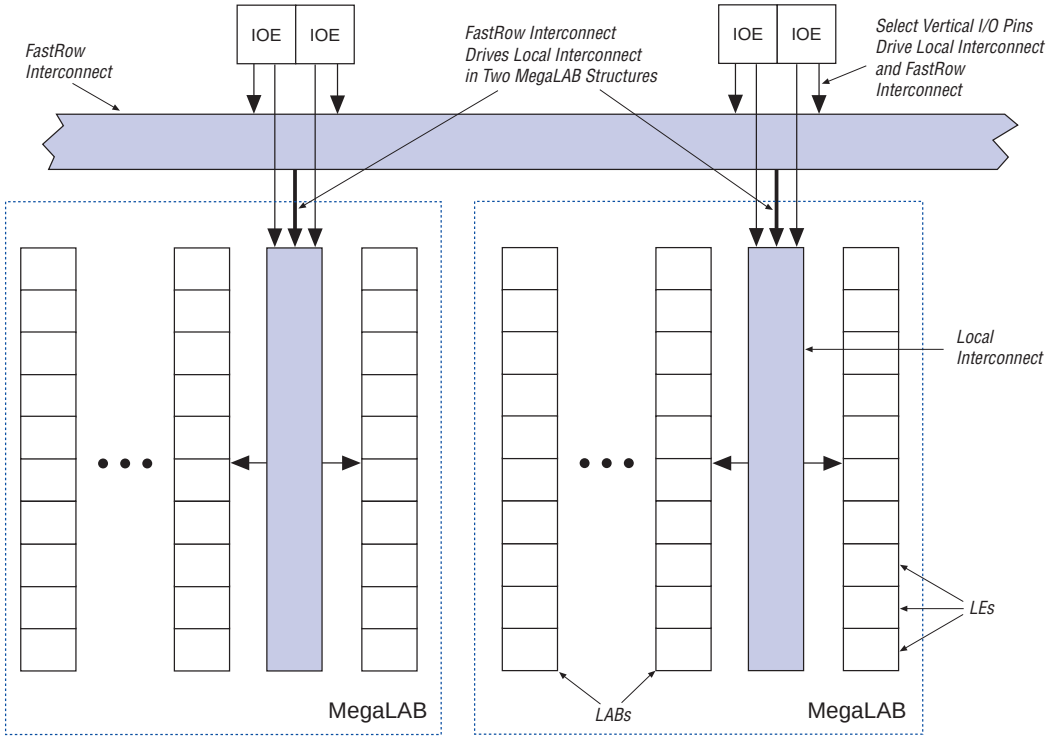
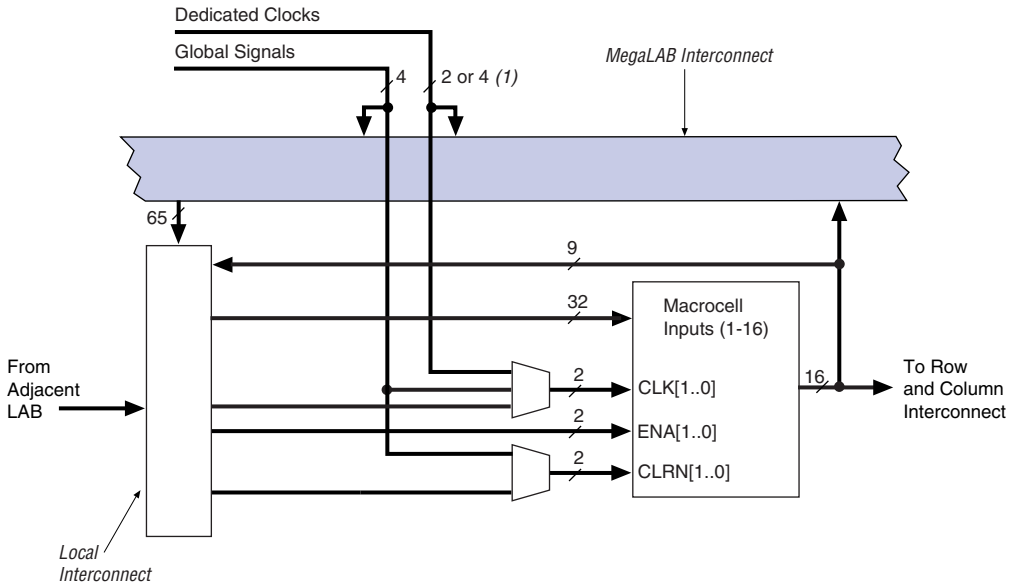


Table 9 summarizes how various elements of the APEX 20K architecture drive each other.

Figure 13. Product-Term Logic in ESB



Note to Figure 13:
(1) APEX 20KE devices have four dedicated clocks.

Macrocells

APEX 20K macrocells can be configured individually for either sequential or combinatorial logic operation. The macrocell consists of three functional blocks: the logic array, the product-term select matrix, and the programmable register.

Combinatorial logic is implemented in the product terms. The product-term select matrix allocates these product terms for use as either primary logic inputs (to the OR and XOR gates) to implement combinatorial functions, or as parallel expanders to be used to increase the logic available to another macrocell. One product term can be inverted; the Quartus II software uses this feature to perform DeMorgan's inversion for more efficient implementation of wide OR functions. The Quartus II software Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset. Figure 14 shows the APEX 20K macrocell.

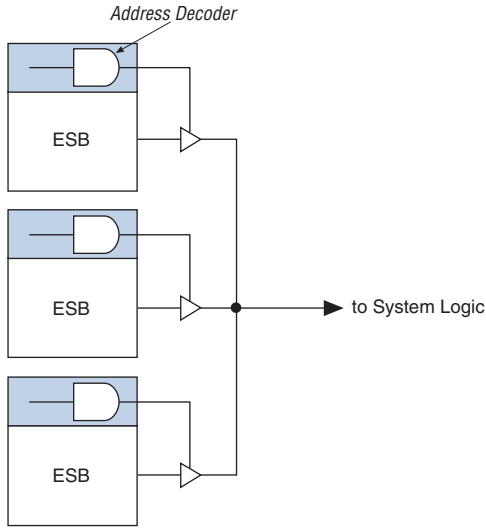
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

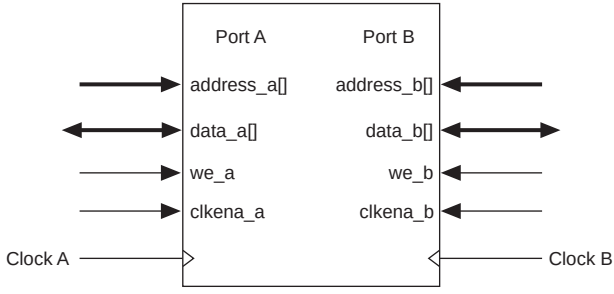
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in Figure 19.

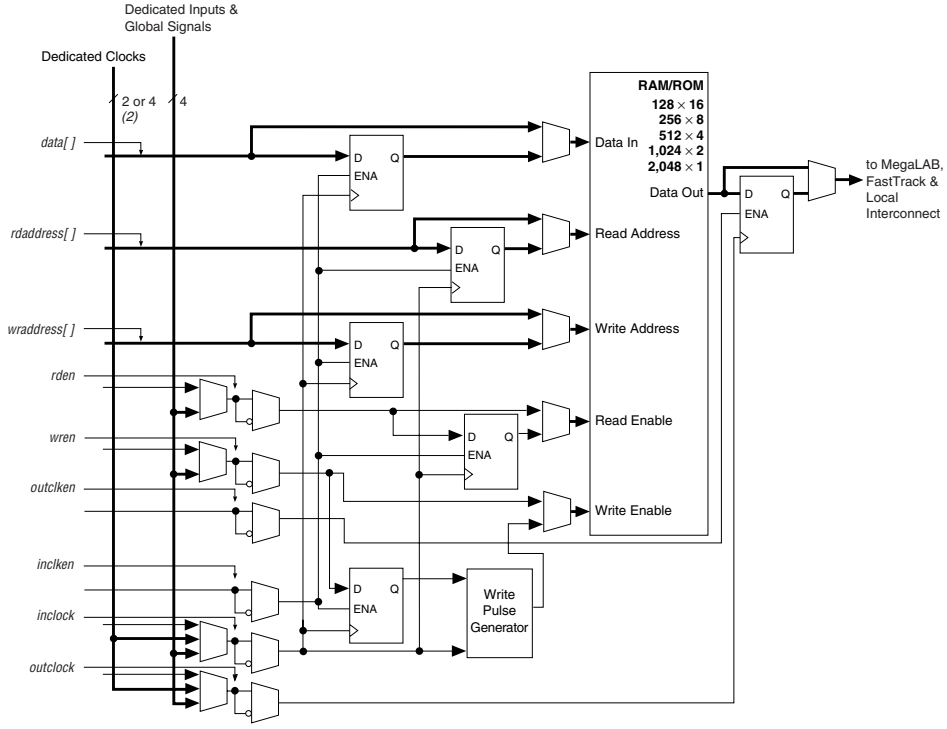
Figure 19. APEX 20K ESB Implementing Dual-Port RAM



Input/Output Clock Mode

The input/output clock mode contains two clocks. One clock controls all registers for inputs into the ESB: data input, WE, RE, read address, and write address. The other clock controls the ESB data output registers. The ESB also supports clock enable and asynchronous clear signals; these signals also control the reading and writing of registers independently. Input/output clock mode is commonly used for applications where the reads and writes occur at the same system frequency, but require different clock enable signals for the input and output registers. Figure 21 shows the ESB in input/output clock mode.

Figure 21. ESB in Input/Output Clock Mode *Note (1)*



Notes to Figure 21:
(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.
(2) APEX 20KE devices have four dedicated clocks.

Single-Port Mode

The APEX 20K ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 22.

Table 28. APEX 20KE Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(5)*, *(6)*	–0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

For DC Operating Specifications on APEX 20KE I/O standards, please refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices).*

Table 30. APEX 20KE Device Capacitance *Note (15)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 27 through 30:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to the voltage shown in the following table based on input duty cycle for input currents less than 100 mA. The overshoot is dependent upon duty cycle of the signal. The DC case is equivalent to 100% duty cycle.

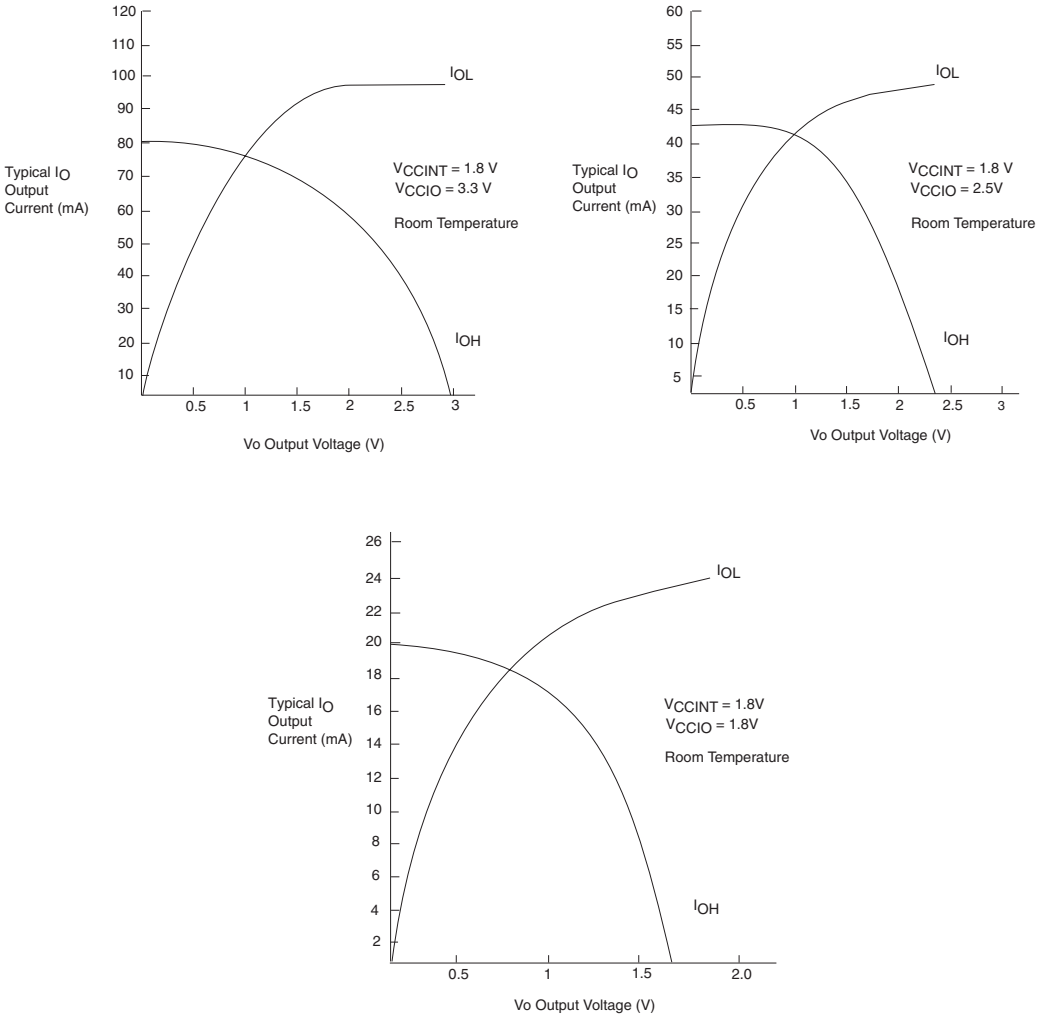
Vin	Max. Duty Cycle
4.0V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%

(6) All pins, including dedicated inputs, clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V or 3.3 V.
(8) These values are specified under the APEX 20KE device recommended operating conditions, shown in Table 24 on page 60.
(9) Refer to *Application Note 117 (Using Selectable I/O Standards in Altera Devices)* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when VCCIO = 1.8 V.
(10) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(11) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(12) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(13) This value is specified for normal device operation. The value may vary during power-up.
(14) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(15) Capacitance is sample-tested only.

Figure 33 shows the relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance on APEX 20K devices.

Figure 35 shows the output drive characteristics of APEX 20KE devices.

Figure 35. Output Drive Characteristics of APEX 20KE Devices *Note (1)*



Note to Figure 35:
(1) These are transient (AC) currents.

Timing Model

The high-performance FastTrack and MegaLAB interconnect routing resources ensure predictable performance, accurate simulation, and accurate timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Note to Tables 32 and 33:
(1) These timing parameters are sample-tested only.

Tables 34 through 37 show APEX 20KE LE, ESB, routing, and functional timing microparameters for the f_{MAX} timing model.

Table 34. APEX 20KE LE Timing Microparameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Table 35. APEX 20KE ESB Timing Microparameters

Symbol	Parameter
t_{ESBARC}	ESB Asynchronous read cycle time
t_{ESBSRC}	ESB Synchronous read cycle time
t_{ESBAWC}	ESB Asynchronous write cycle time
t_{ESBSWC}	ESB Synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
t_{ESBWEH}	ESB WE hold time after clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBDATAH}$	ESB data hold time after clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATACO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATACO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB Macrocell input to non-registered output
$t_{PTERMSU}$	ESB Macrocell register setup time before clock
$t_{PTERMCO}$	ESB Macrocell register clock-to-output delay

Table 36. APEX 20KE Routing Timing Microparameters Note (1)	
Symbol	**Parameter**
t_{F1-4}	Fanout delay using Local Interconnect
t_{F5-20}	Fanout delay estimate using MegaLab Interconnect
t_{F20+}	Fanout delay estimate using FastTrack Interconnect

Note to Table 36:

(1) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

Table 37. APEX 20KE Functional Timing Microparameters	
Symbol	**Parameter**
TCH	Minimum clock high time from clock pin
TCL	Minimum clock low time from clock pin
TCLRP	LE clear Pulse Width
TPREP	LE preset pulse width
TESBCH	Clock high time for ESB
TESBCL	Clock low time for ESB
TESBWP	Write pulse width
TESBRP	Read pulse width

Tables 38 and 39 describe the APEX 20KE external timing parameters.

Table 38. APEX 20KE External Timing Parameters Note (1)		
Symbol	**Clock Parameter**	**Conditions**
t_{INSU}	Setup time with global clock at IOE input register	
t_{INH}	Hold time with global clock at IOE input register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE output register	C1 = 10 pF
$t_{INSUPLL}$	Setup time with PLL clock at IOE input register	
t_{INHPLL}	Hold time with PLL clock at IOE input register	
$t_{OUTCOPLL}$	Clock-to-output delay with PLL clock at IOE output register	C1 = 10 pF

Table 42. EP20K400 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.1		0.3		0.6		ns
t_{H}	0.5		0.8		0.9		ns
t_{CO}		0.1		0.4		0.6	ns
t_{LUT}		1.0		1.2		1.4	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.5		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.1		3.6	ns
$t_{PTERMSU}$	1.7		2.1		2.4		ns
$t_{PTERMCO}$		1.0		1.2		1.4	ns
t_{F1-4}		0.4		0.5		0.6	ns
t_{F5-20}		2.6		2.8		2.9	ns
t_{F20+}		3.7		3.8		3.9	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.5		0.6		0.8		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.5		1.9		2.2		ns
t_{ESBRP}	1.0		1.2		1.4		ns

Tables 43 through 48 show the I/O external and external bidirectional timing parameter values for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 43. EP20K100 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	2.3		2.8		3.2		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	4.8	ns

Table 44. EP20K100 External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ (1)	2.3		2.8		3.2		ns
$t_{INHBIDIR}$ (1)	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$ (1)	2.0	4.5	2.0	4.9	2.0	6.6	ns
$t_{XZBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{ZXBIDIR}$ (1)		5.0		5.9		6.9	ns
$t_{INSUBIDIR}$ (2)	1.0		1.2		–		ns
$t_{INHBIDIR}$ (2)	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ (2)	0.5	2.7	0.5	3.1	–	–	ns
$t_{XZBIDIR}$ (2)		4.3		5.0		–	ns
$t_{ZXBIDIR}$ (2)		4.3		5.0		–	ns

Table 45. EP20K200 External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU} (1)	1.9		2.3		2.6		ns
t_{INH} (1)	0.0		0.0		0.0		ns
t_{OUTCO} (1)	2.0	4.6	2.0	5.6	2.0	6.8	ns
t_{INSU} (2)	1.1		1.2		–		ns
t_{INH} (2)	0.0		0.0		–		ns
t_{OUTCO} (2)	0.5	2.7	0.5	3.1	–	–	ns

Notes to Tables 43 through 48:
(1) This parameter is measured without using ClockLock or ClockBoost circuits.
(2) This parameter is measured using ClockLock or ClockBoost circuits.

Tables 49 through 54 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K30E APEX 20KE devices.

Table 49. EP20K30E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.02		0.02		ns
t_{H}	0.11		0.16		0.23		ns
t_{CO}		0.32		0.45		0.67	ns
t_{LUT}		0.85		1.20		1.77	ns

Table 74. EP20K200E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.68		2.06		2.24	ns
t_{ESBSRC}		2.27		2.77		3.18	ns
t_{ESBAWC}		3.10		3.86		4.50	ns
t_{ESBSWC}		2.90		3.67		4.21	ns
$t_{ESBWASU}$	0.55		0.67		0.74		ns
t_{ESBWAH}	0.36		0.46		0.48		ns
$t_{ESBWDSU}$	0.69		0.83		0.95		ns
t_{ESBWDH}	0.36		0.46		0.48		ns
$t_{ESBRASU}$	1.61		1.90		2.09		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.42		1.71		2.01		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.06		-0.07		0.05		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.13		0.31		ns
$t_{ESBRADDRSU}$	0.18		0.23		0.39		ns
$t_{ESBDATACO1}$		1.09		1.35		1.51	ns
$t_{ESBDATACO2}$		2.19		2.75		3.22	ns
t_{ESBDD}		2.75		3.41		4.03	ns
t_{PD}		1.58		1.97		2.33	ns
$t_{PTERMSU}$	1.00		1.22		1.51		ns
$t_{PTERMCO}$		1.10		1.37		1.09	ns

Table 75. EP20K200E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.27		0.29	ns
t_{F5-20}		1.02		1.20		1.41	ns
t_{F20+}		1.99		2.23		2.53	ns

Table 76. EP20K200E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.44		2.65		ns
t_{CL}	1.36		2.44		2.65		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.36		2.44		2.65		ns
t_{ESBCL}	1.36		2.44		2.65		ns
t_{ESBWP}	1.18		1.48		1.76		ns
t_{ESBRP}	0.95		1.17		1.41		ns

Table 77. EP20K200E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.24		2.35		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{INSUPLL}$	2.13		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.01	0.50	3.36	-	-	ns

Table 87. EP20K400E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.25		0.26	ns
t_{F5-20}		1.01		1.12		1.25	ns
t_{F20+}		3.71		3.92		4.17	ns

Table 88. EP20K400E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.22		2.35		ns
t_{CL}	1.36		2.26		2.35		ns
t_{CLRP}	0.18		0.18		0.19		ns
t_{PREP}	0.18		0.18		0.19		ns
t_{ESBCH}	1.36		2.26		2.35		ns
t_{ESBCL}	1.36		2.26		2.35		ns
t_{ESBWP}	1.17		1.38		1.56		ns
t_{ESBRP}	0.94		1.09		1.25		ns

Table 89. EP20K400E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.51		2.64		2.77		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{INSUPLL}$	3.221		3.38		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.45	-	-	ns

Version 4.1

APEX 20K Programmable Logic Device Family Data Sheet version 4.1 contains the following changes:

- t_{ESBWEH} added to Figure 37 and Tables 35, 50, 56, 62, 68, 74, 86, 92, 97, and 104.
- Updated EP20K300E device internal and external timing numbers in Tables 79 through 84.